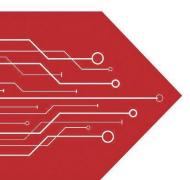
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Product data sheet

www.msksemi.com







80W peak pulse power per line ($t_P = 8/20\mu s$)

Replacement for MLV(0402)

Bidirectional configurations

Response time is typically < 1ns

Low clamping voltage

RoHS compliant

Transient protection for data lines to

IEC61000-4-2(ESD) ±30KV(air), ±30KV(contact);

IEC61000-4-4 (EFT) 40A (5/50ns)

Mechanical Characteristics

Lead finish:100% matte Sn(Tin)

Mounting position: Any

Qualified max reflow temperature:260°C

Device meets MSL 2 requirements

Pure tin plating: 7 ~ 17 um

Pin flatness:≤3mil

Applications

Cellular phones

Portable devices

Digital cameras

Power supplies



DFN1006P2X

Electrical characteristics per line@25℃ (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	VRWM				8	٧
Breakdown Voltage	V _{BR}	It= 1mA	9.0	11.0	13.0	V
Reverse Leakage Current	lr	V _{RWM} = 5V T=25°C			1.0	μA
Maximum Reverse Peak Pulse	I PP			5.0		А
Clamping Voltage	Vc	Ipp=1A			13	V
Clamping Voltage	Vc	Ipp=3A			15	V
Clamping Voltage	Vc	Ipp=5A			17	V
Junction Capacitance	Cj	V _R =0V f = 1MHz		13	15	pF

Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Peak Pulse Power (t _p =8/20μs)	P _{pp}	80	W
Operating Temperature	TJ	-55 to +150	$^{\circ}\!\mathrm{C}$
Storage Temperature	T _{STG}	-55 to +150	$^{\circ}\!$





Electrical Parameter

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @ IPP
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
Ι _Τ	Test Current
V _{BR}	Breakdown Voltage @ I⊤

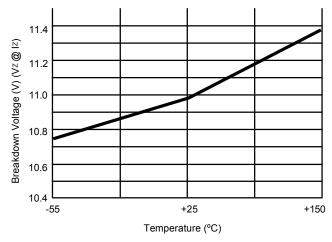
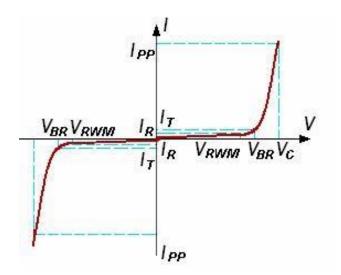


Fig . Typical Breakdown Voltage vs. Temperature



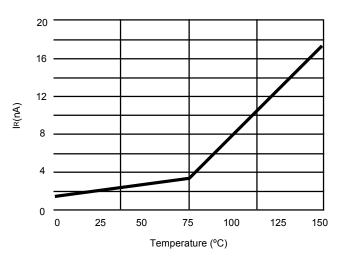


Fig .Typical Leakage Current vs. Temperature

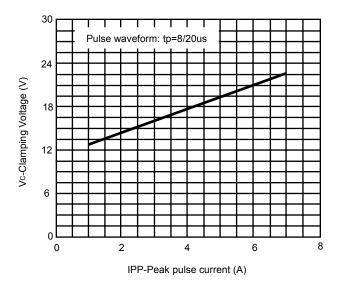
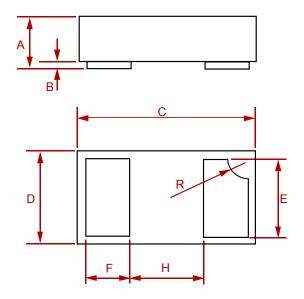


Fig Clamping voltage vs. Peak pulse current



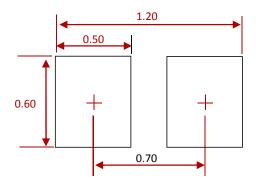


PACKAGE MECHANICAL DATA



Dim	Inc	hes	Millimeters		
	MIN	MAX	MIN	MAX	
Α	0.0125	0.02	0.32	0.52	
В	0.000	0.002	0.00	0.05	
С	0.037	0.043	0.95	1.080	
D	0.022	0.027	0.55	0.680	
E	0.016	0.024	0.40	0.60	
F	0.008	0.012	0.20	0.30	
Н	0.015Typ.		0.40Typ.		
R	0.001	0.005	0.05	0.15	

Suggested Pad Layout



NOTES:

- 1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
- 2. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.

REEL SPECIFICATION

P/N	PKG	QTY
AZ4208-01F-MS	DFN1006P2X	12000

Semiconductor Compiance

Attention

- Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.
- MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specificationsof any andall MSKSEMI Semiconductor products described orcontained herein.
- Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- MSKSEMI Semiconductor, strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possiblethat these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuitsfor safedesign, redundant design, and structural design.
- In the event that any or all MSKSEMI Semiconductor products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringementsof intellectual property rights or other rightsof third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.

单击下面可查看定价,库存,交付和生命周期等信息

>>MSKSEMI (美森科)